

DERWENT-ACC-NO: 2003-011115

DERWENT-WEEK: 200301

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TITLE: Semiconductor memory device

INVENTOR: LEE, C H

PATENT-ASSIGNEE: SAMSUNG ELECTRONICS CO LTD [SMSU]

PRIORITY-DATA: 2000KR-0076513 (December 14, 2000)

PATENT-FAMILY:

PUB-NO	PUB-DATE	
LANGUAGE	PAGES	MAIN-IPC
KR 2002047876 A	June 22, 2002	N/A
001	G11C 011/413	

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR2002047876A	N/A	2000KR-
0076513	December 14, 2000	

INT-CL (IPC): G11C011/413

ABSTRACTED-PUB-NO: KR2002047876A

BASIC-ABSTRACT:

NOVELTY - A semiconductor memory device is provided to exactly generate a precharge enable signal and a write enable signal even though a size of a device changes.

DETAILED DESCRIPTION - An inverter(I3) and an inverter(I4) delay a precharge enable signal (S1) and generate a signal (S21). A NAND

gate(NA2) performs a NAND operation of a signal(S3) and a column selecting signal(y1). A NOR gate(NOR) performs a NOR operation of an output signal of the inverter(I3) and an output signal of the NAND gate(NA2) to generate a signal(S41). The signal(S21) is generated in response to the precharge enable signal(S1). The signal(S41) is generated by performing a NAND operation of the write enable signal(S3) and the column selecting signal(y1) in response to the precharge enable signal(S1). A control signal generating circuit generates the precharge enable signal(S1) and a write enable signal(S3) in response to a clock signal and a write enable signal.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: SEMICONDUCTOR MEMORY DEVICE

DERWENT-CLASS: U14

EPI-CODES: U14-A07; U14-A08;

